

FIG. 1A

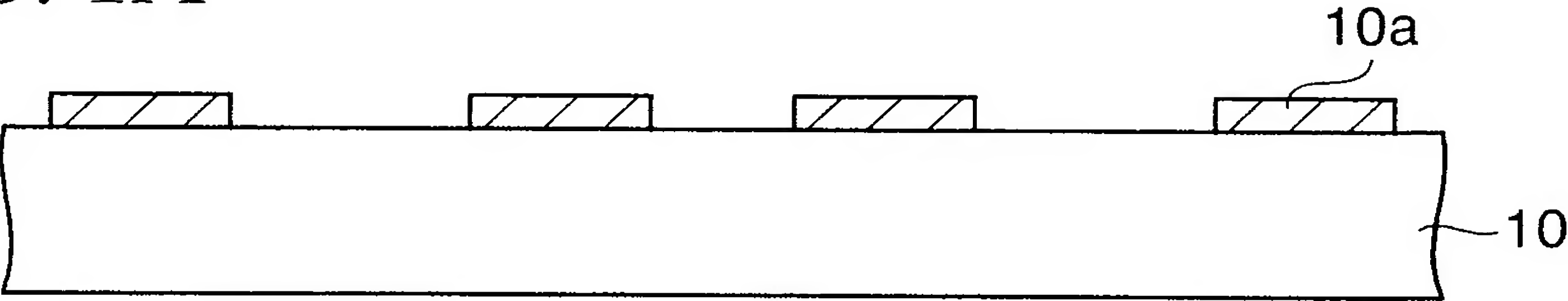


FIG. 1B

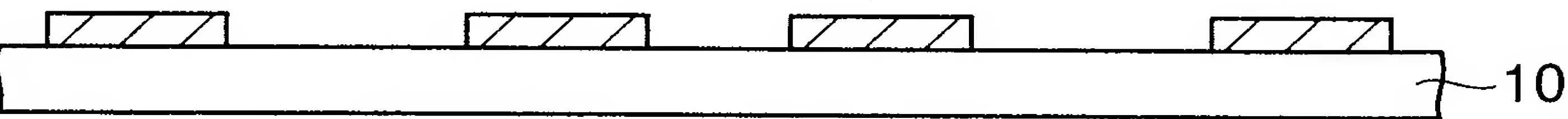


FIG. 1C

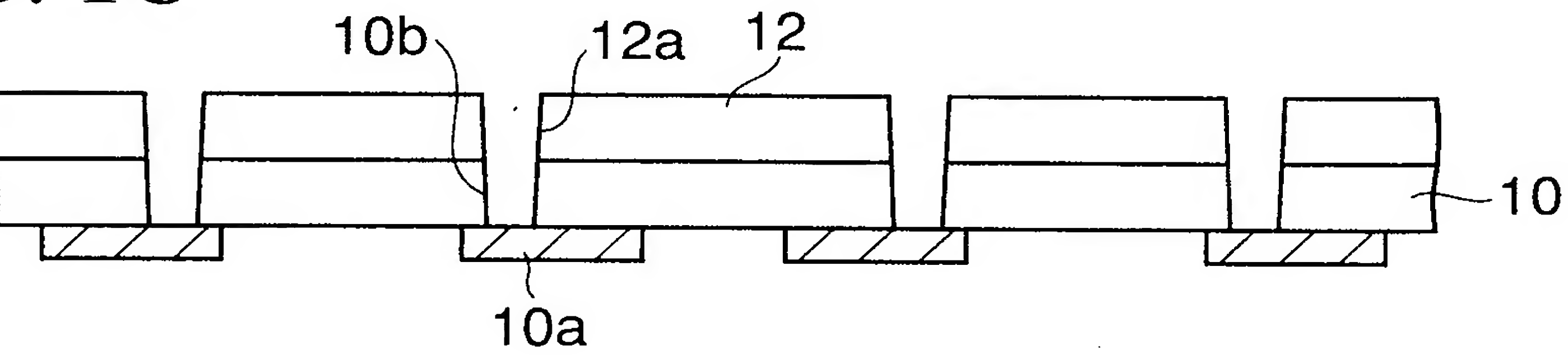


FIG. 1D

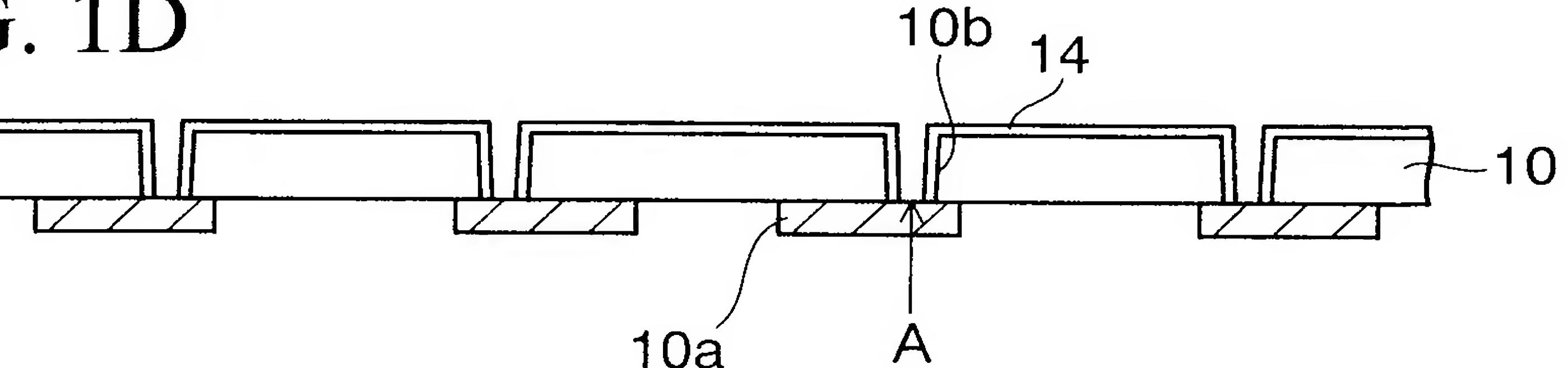


FIG. 1E

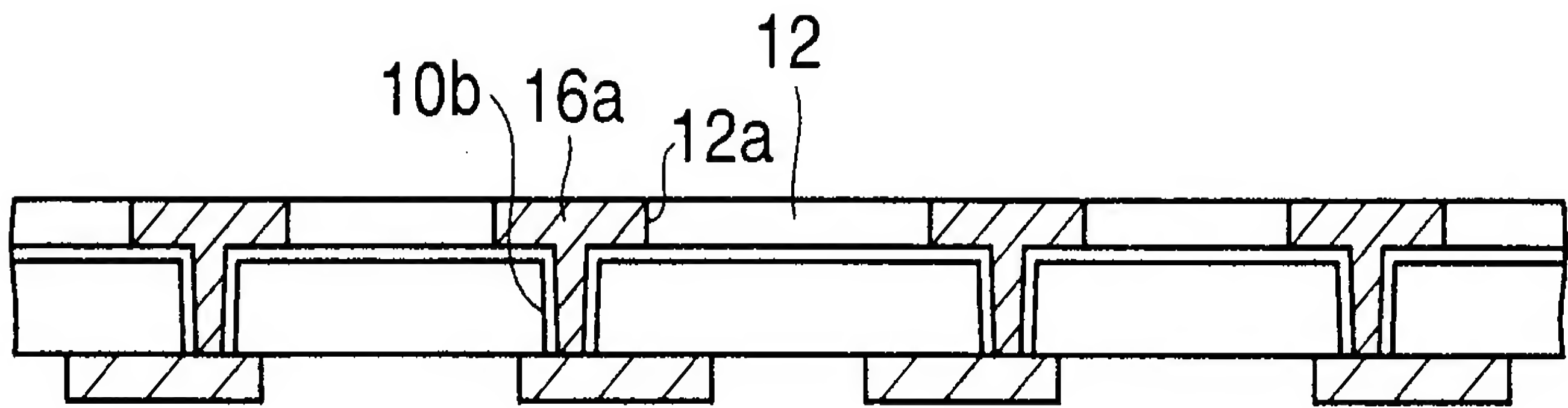


FIG. 1F

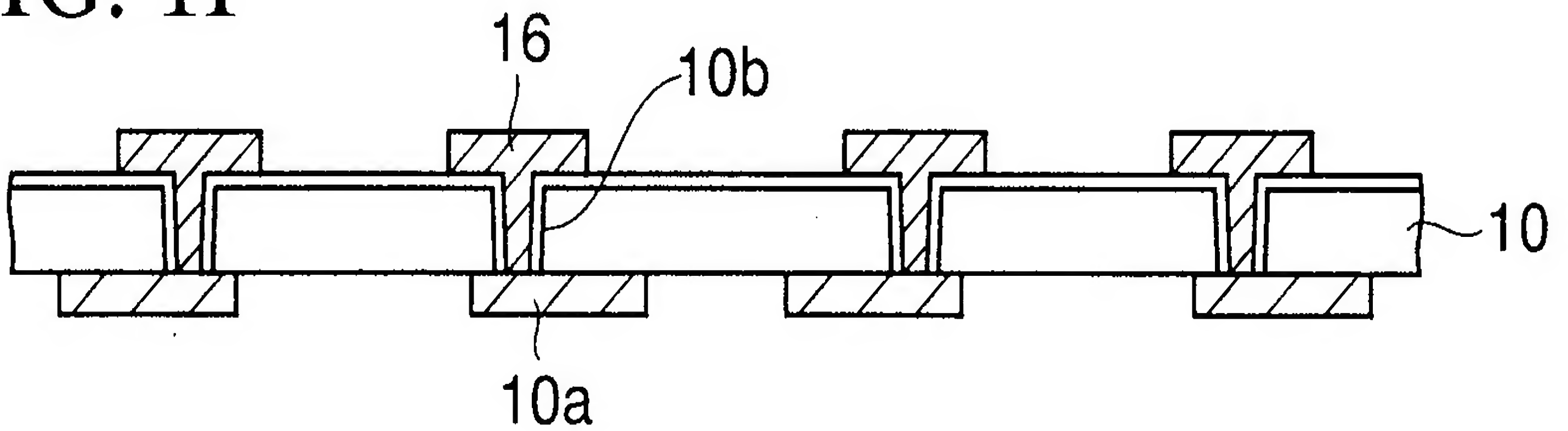


FIG. 1G

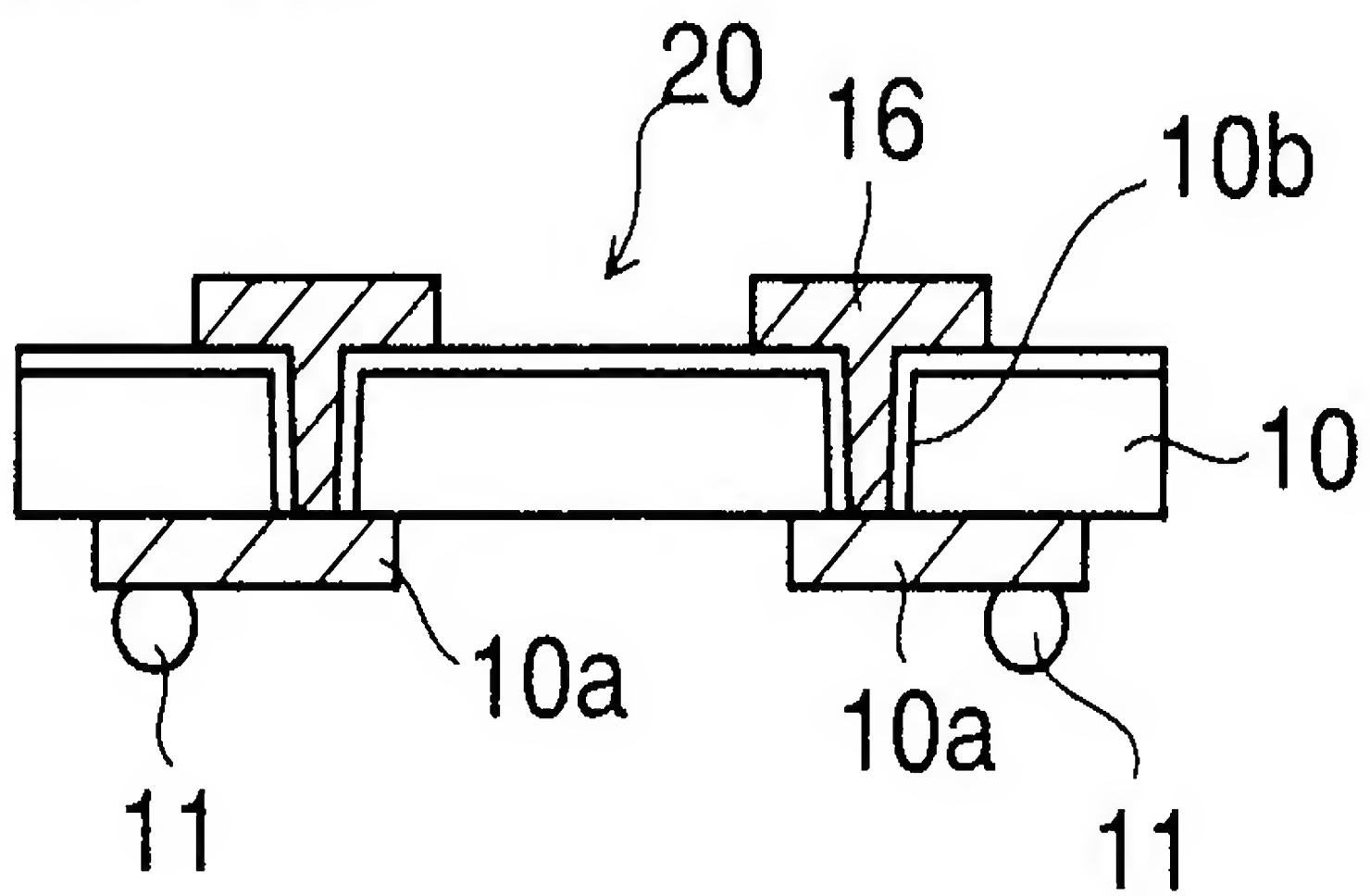


FIG. 1K

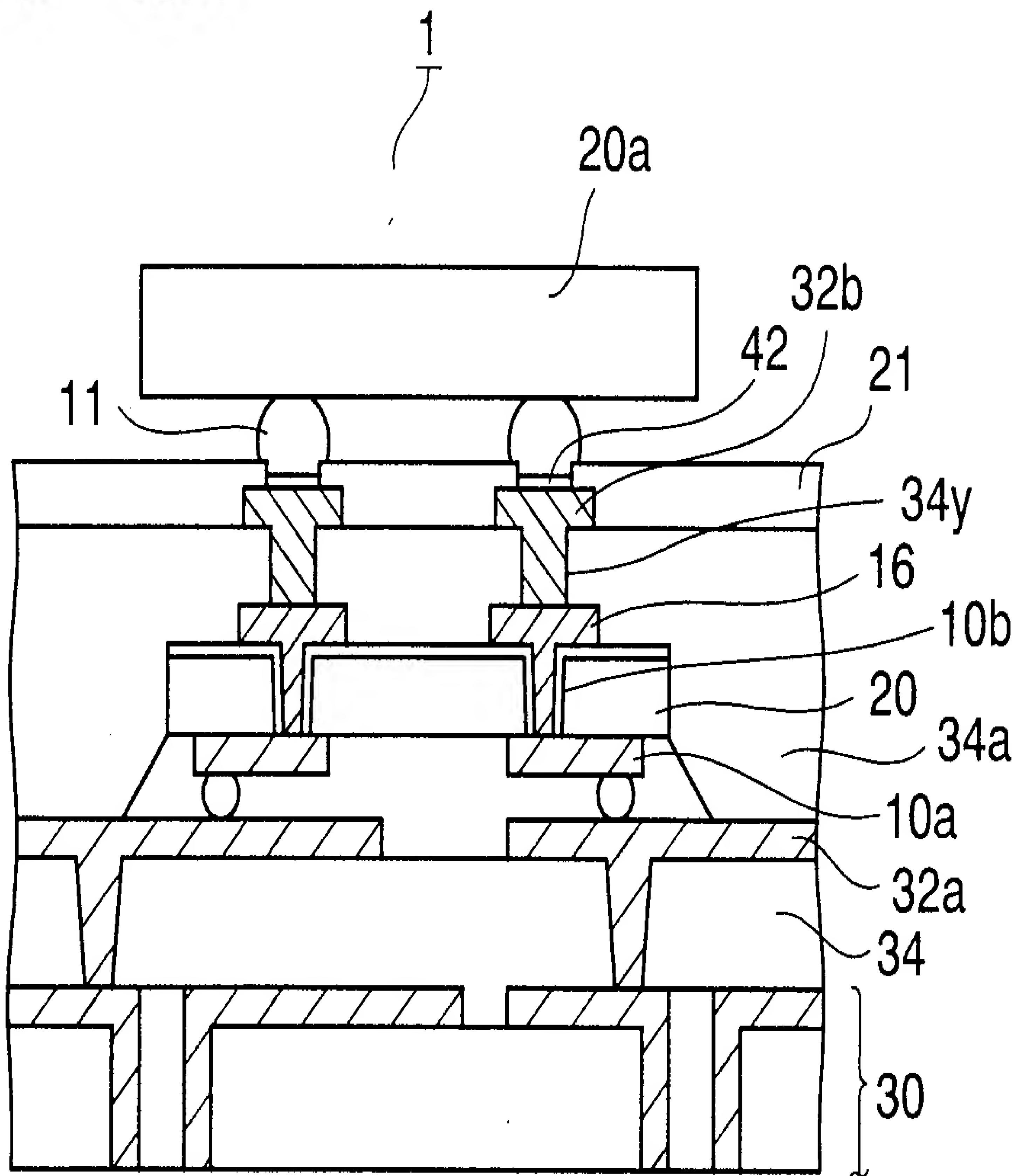


FIG. 2A

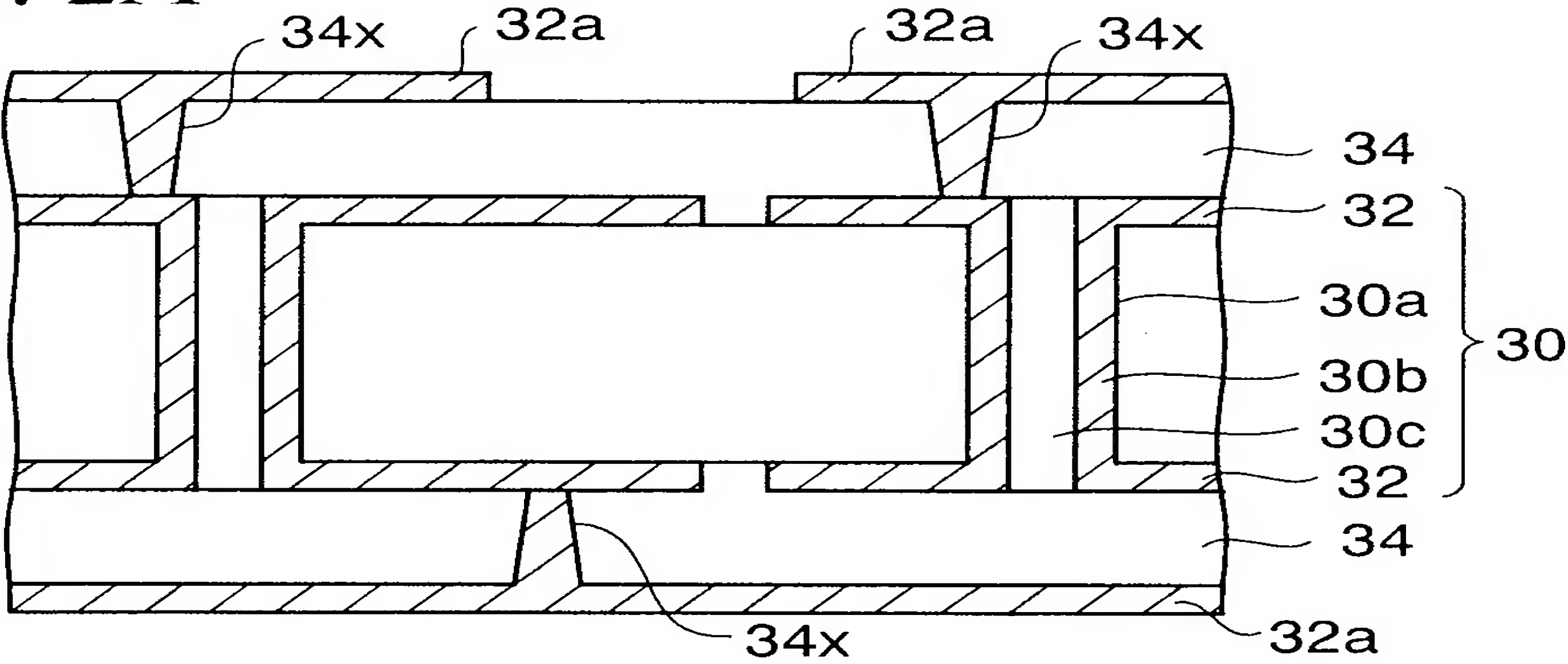


FIG. 2B

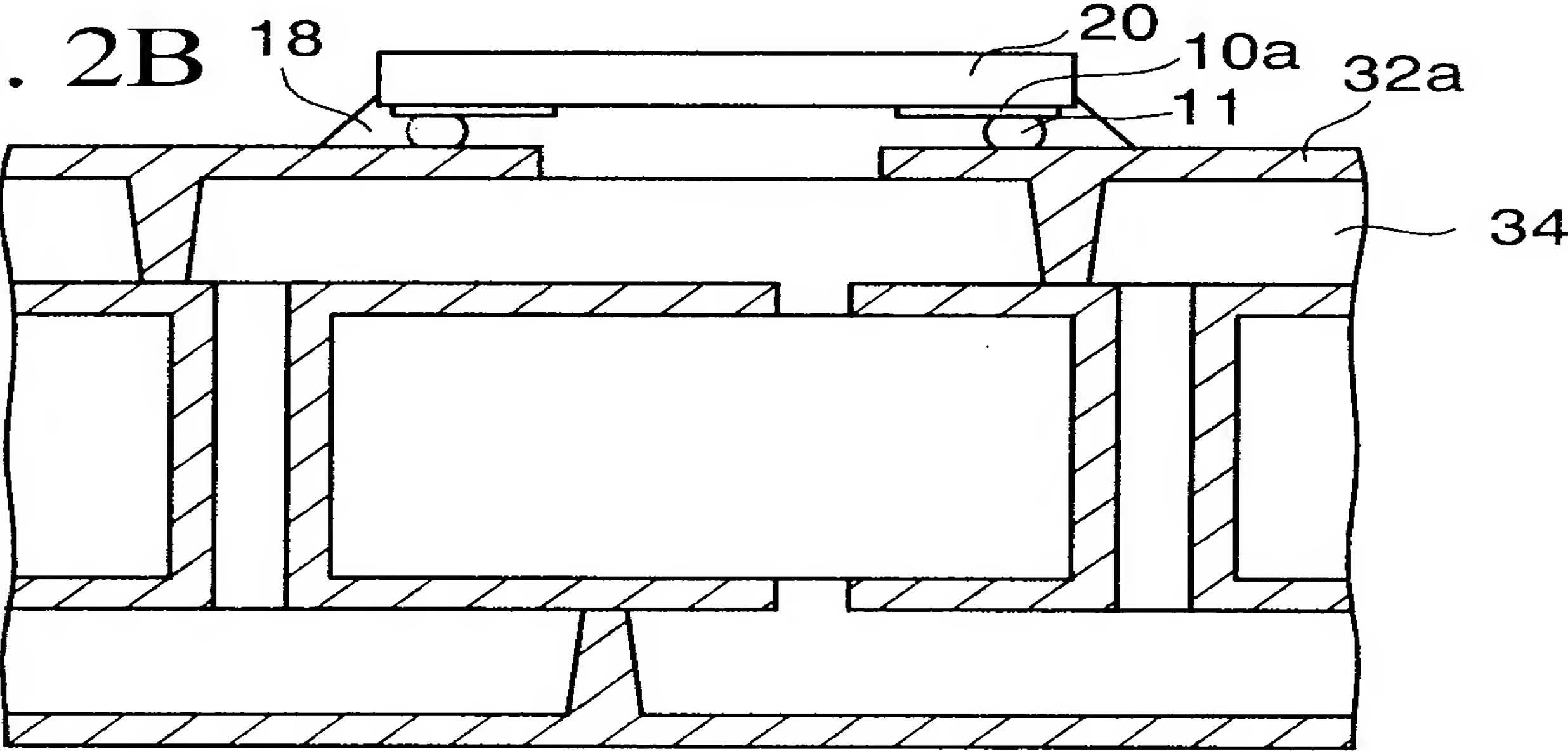


FIG. 2C

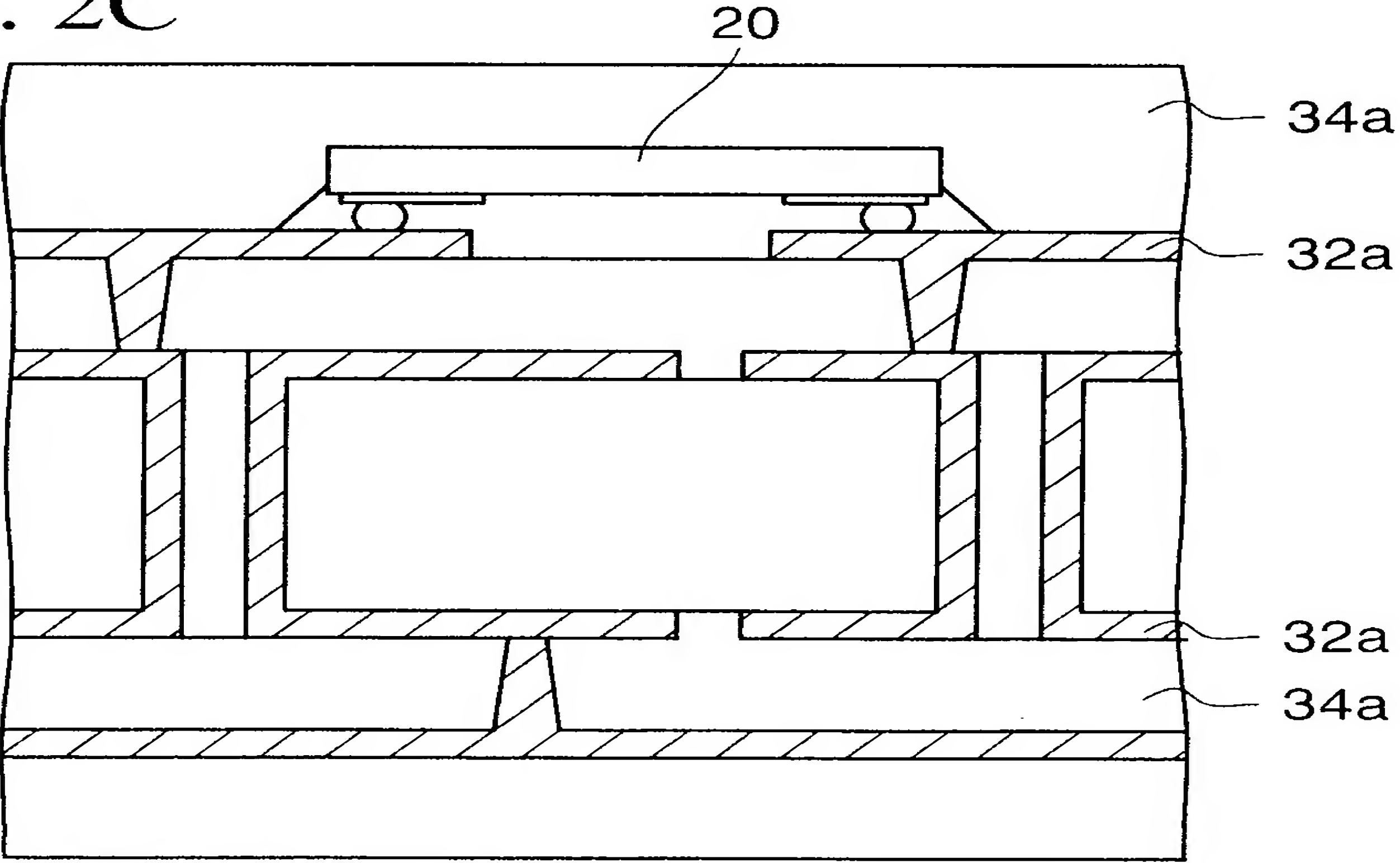


FIG. 2D

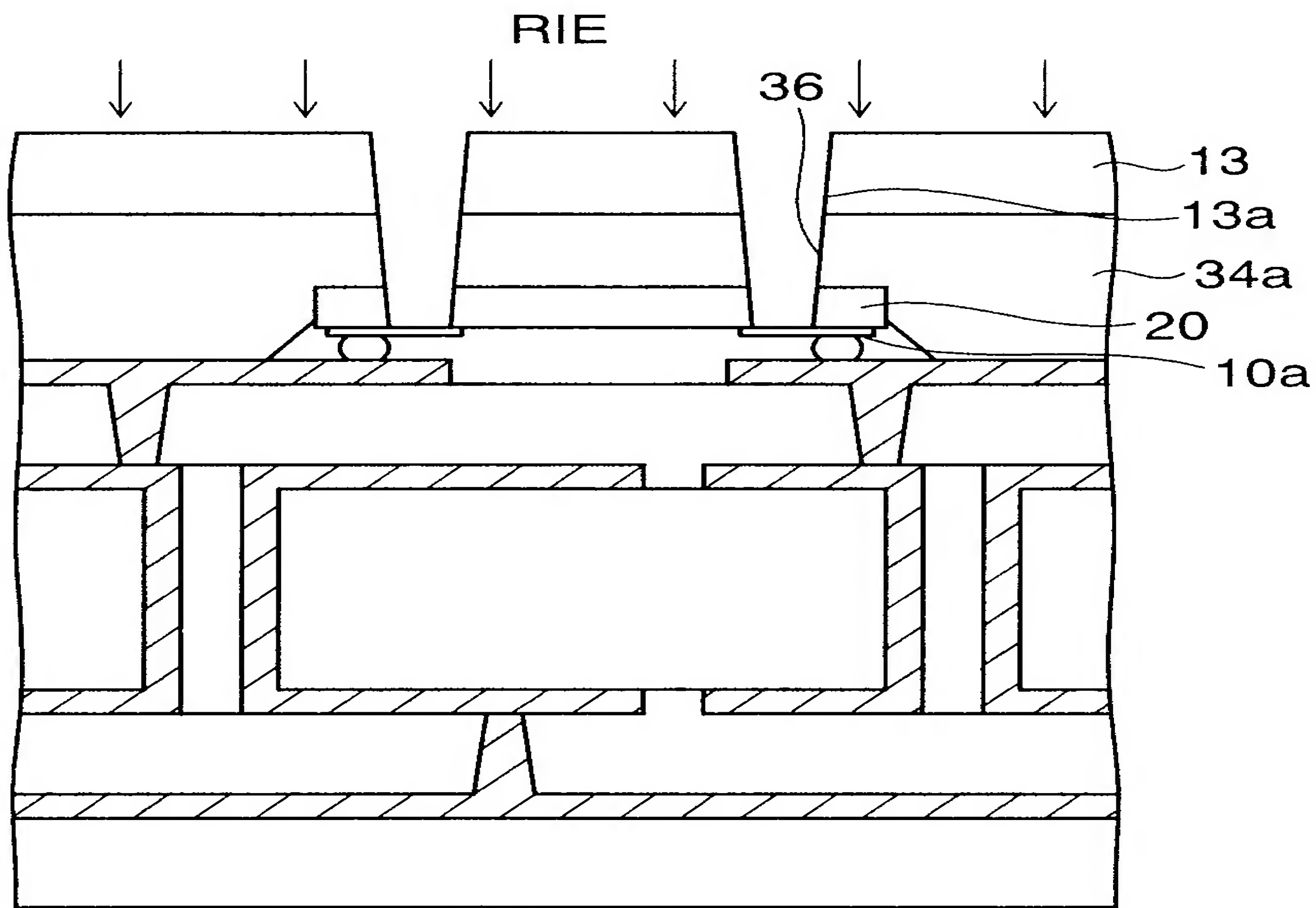


FIG. 2E

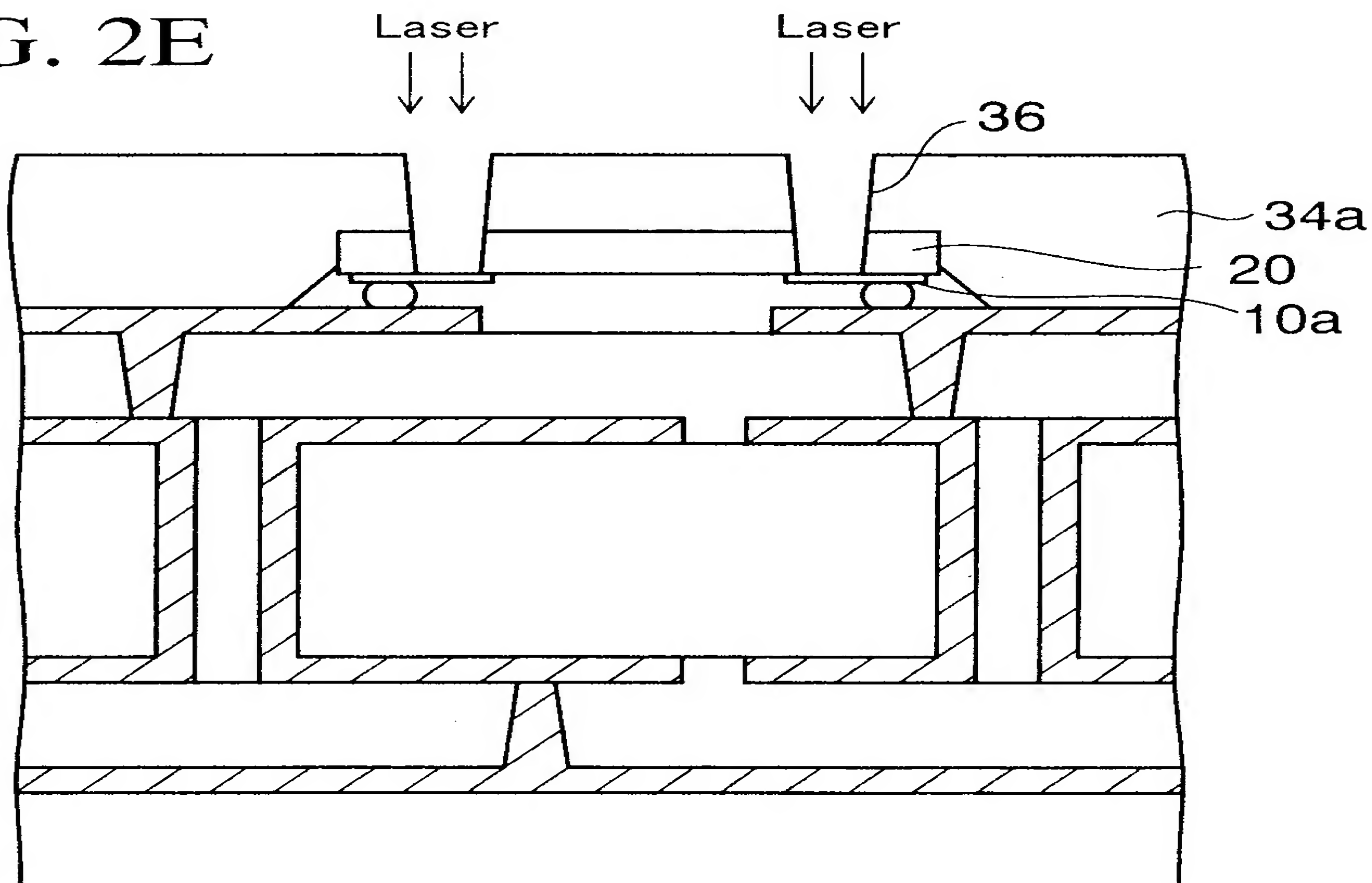


FIG. 2F

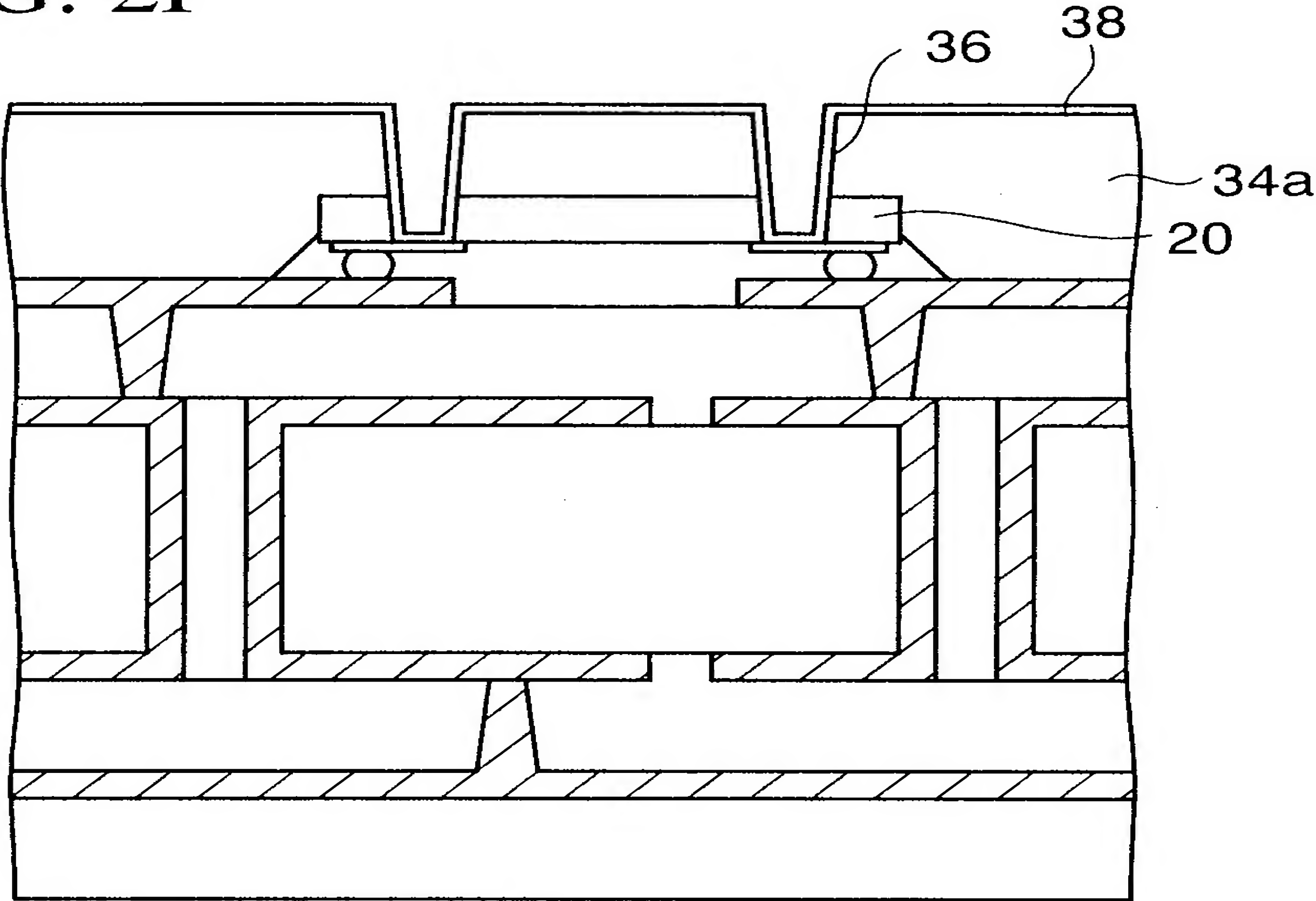


FIG. 2G

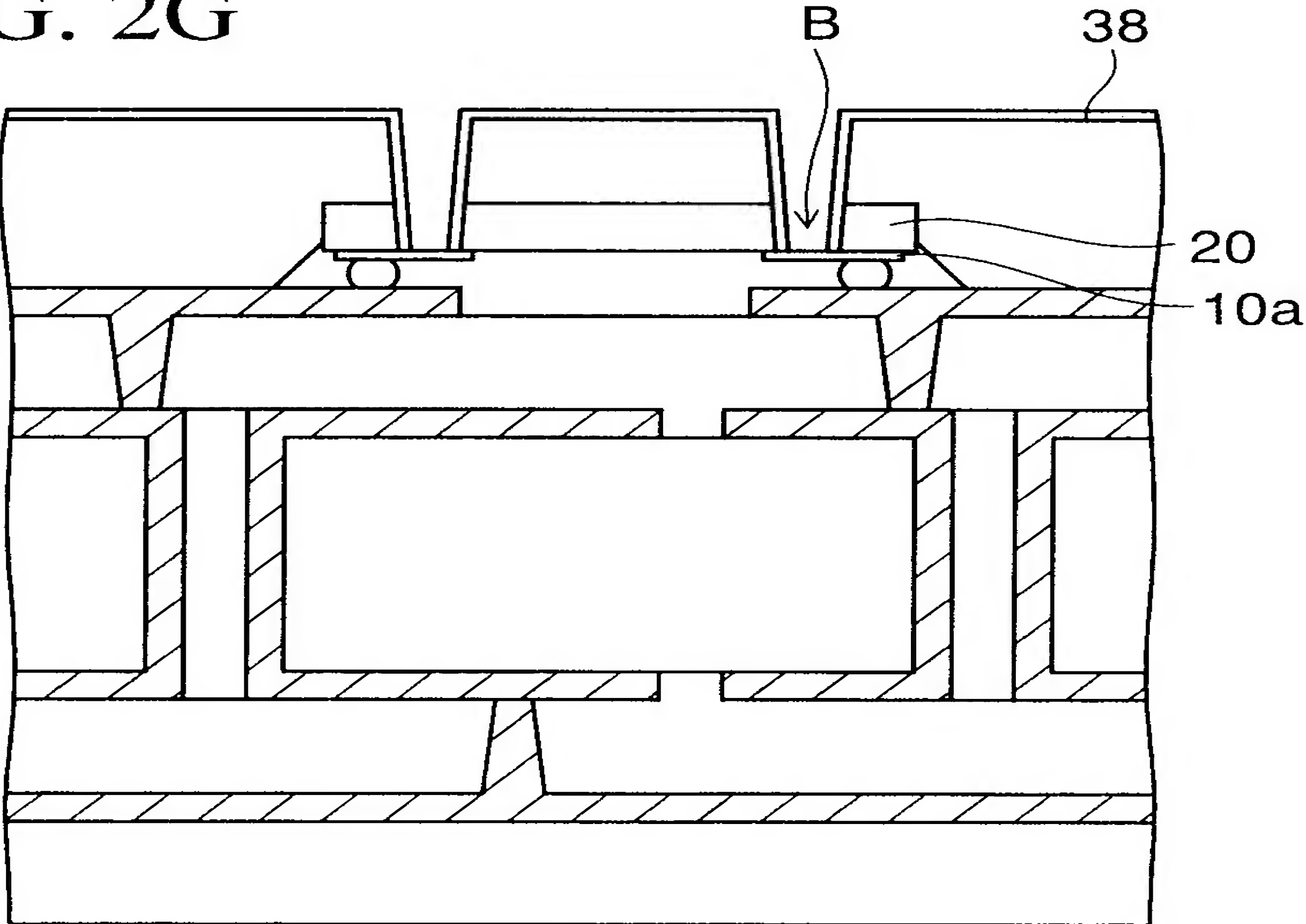


FIG. 2H

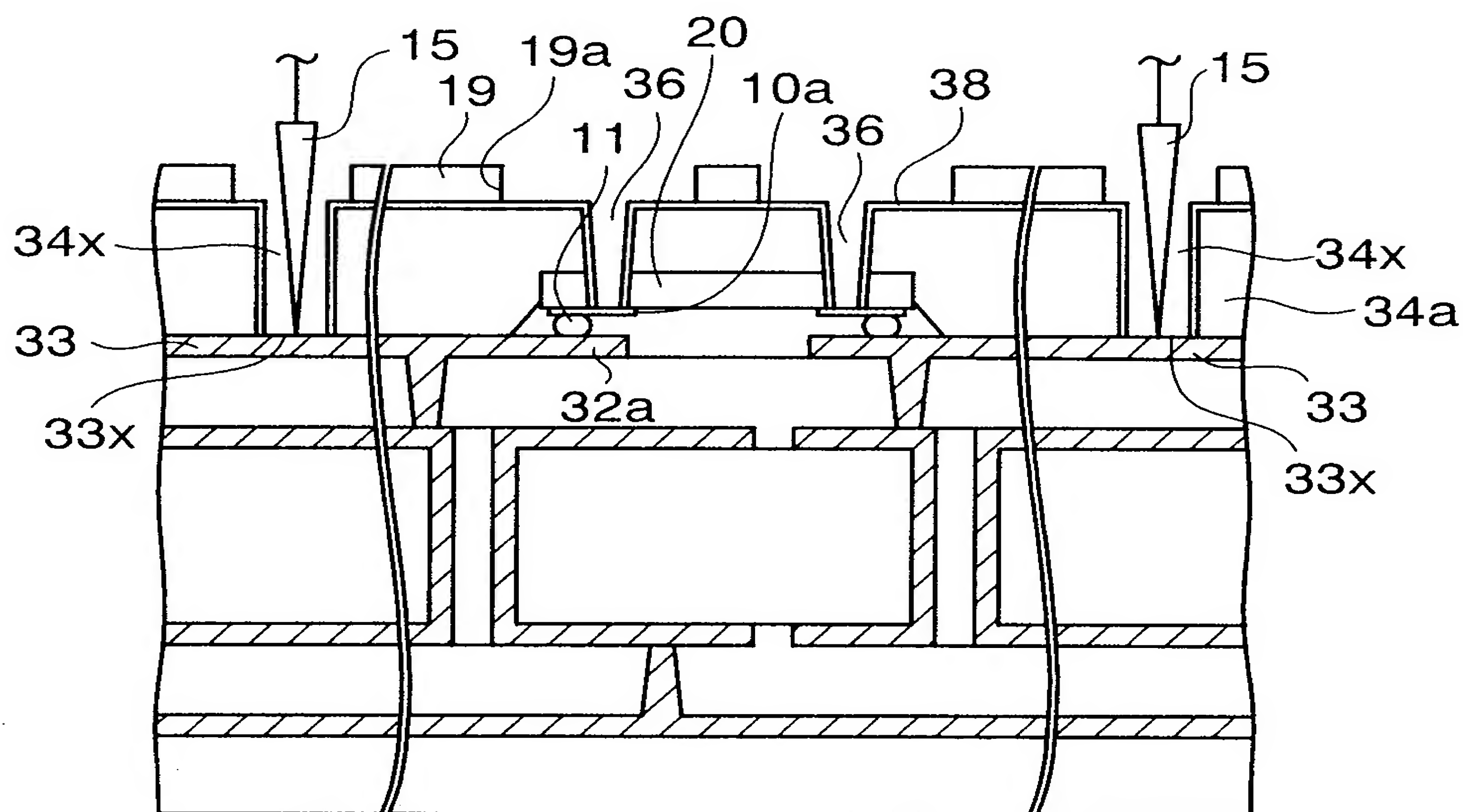
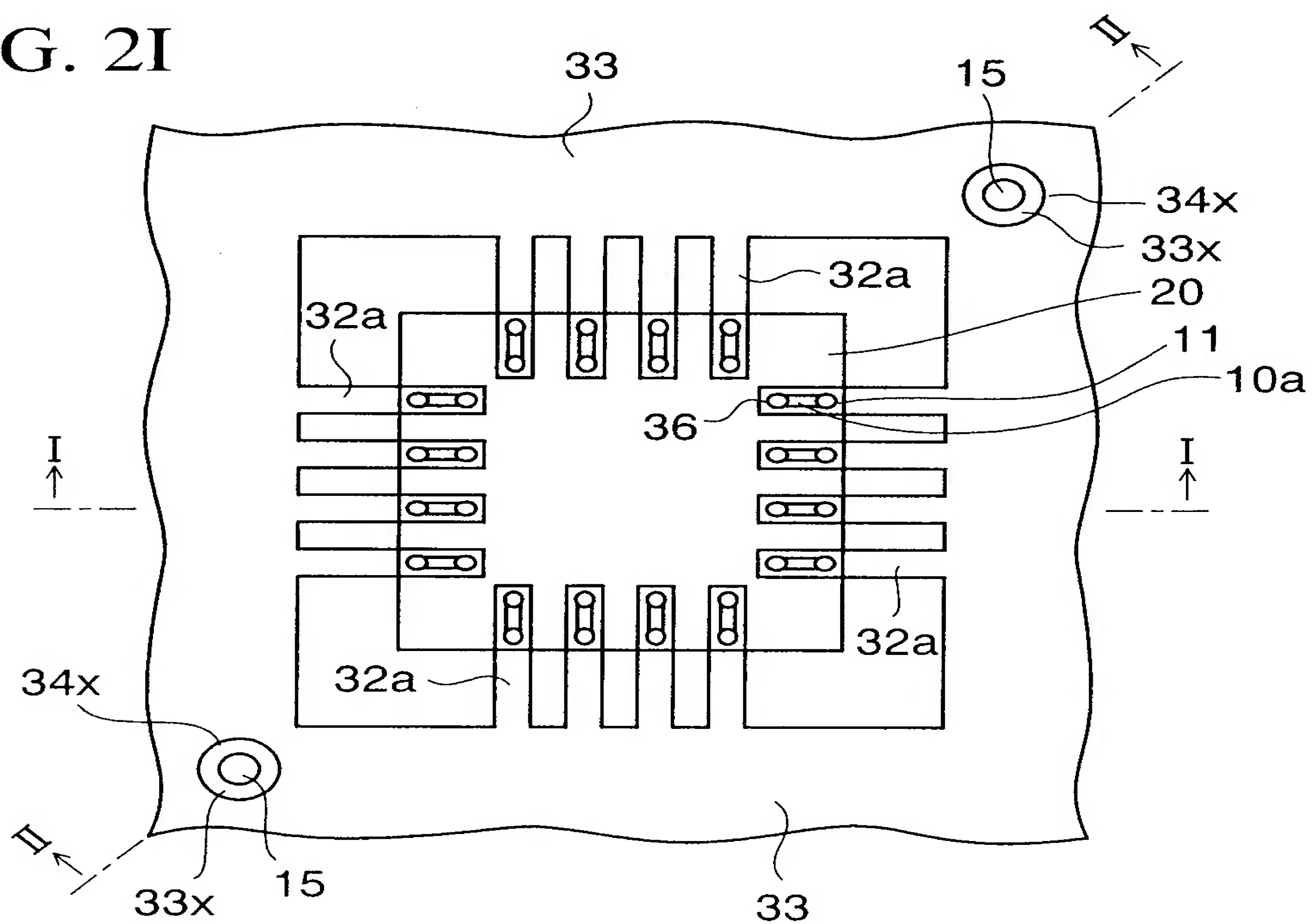


FIG. 2I



[illegible]

FIG. 2K

FIG. 2K is a cross-sectional view of a semiconductor device. The device features a central core (30) with a top layer (20a) and a bottom layer (21). The core is surrounded by a stack of layers (33, 33x, 34a, 34y) and a top layer (42). The device is shown with "Scrapped portion" labels and arrows indicating the removal of the top and bottom layers.

FIG. 2L

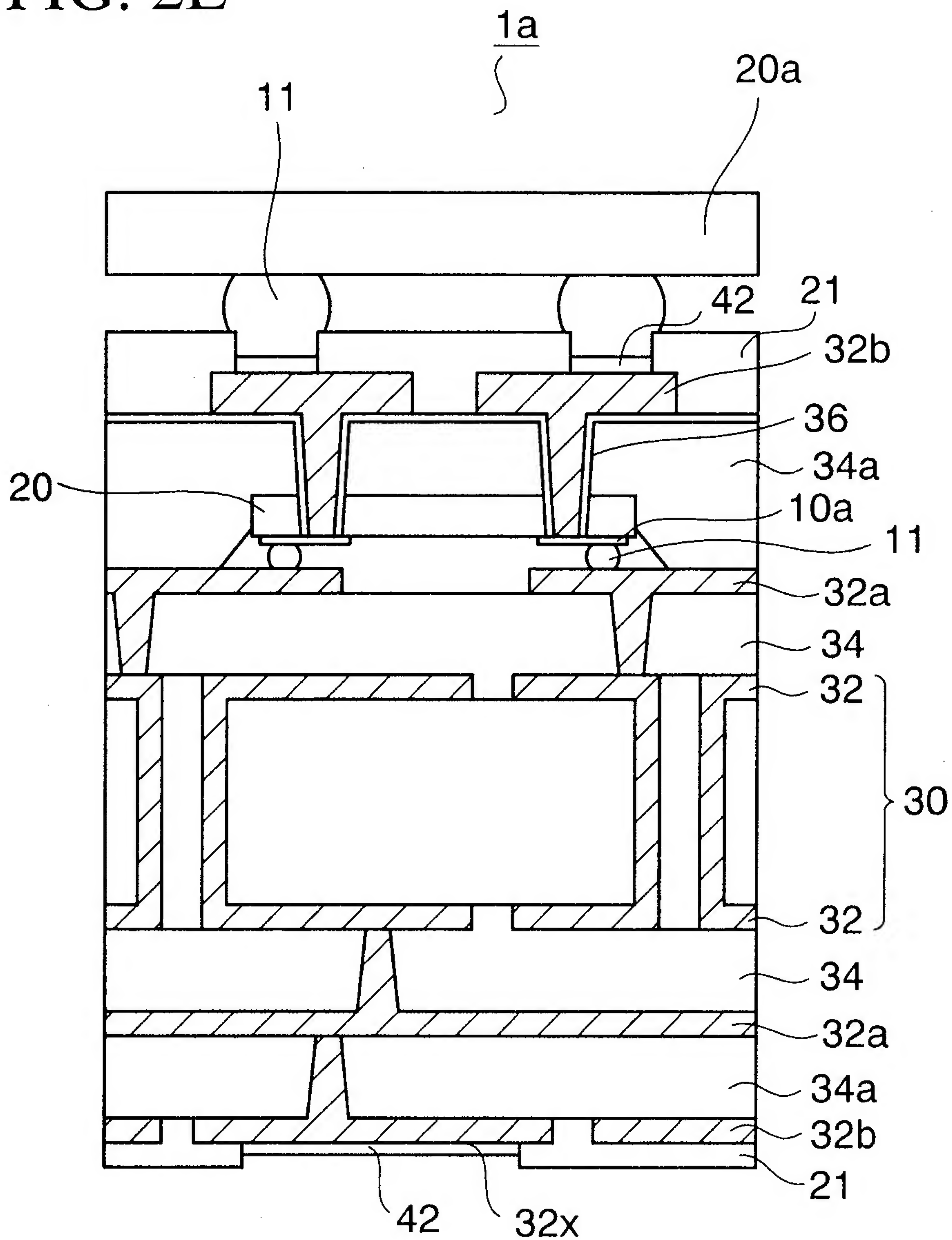


FIG. 3

